

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
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TYPE : 6PT3310N3T**

CHIP SIZE	1.4 * 1.4 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	7,550 pcs

Maximum Ratings (Ta=25°C)

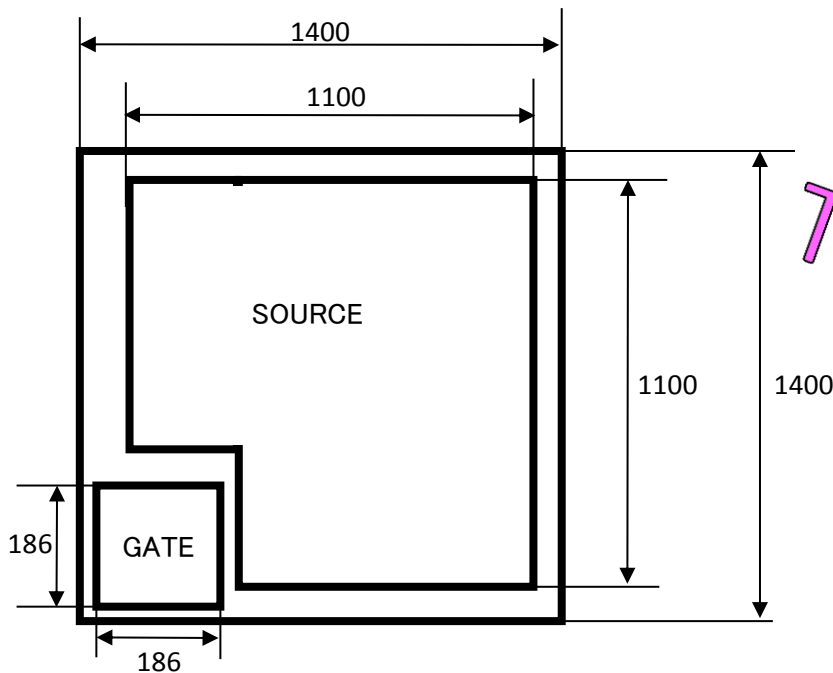
Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	100	V
Gate-source voltage	VGSS	±20	V
Drain Current (DC)	ID	2	A

* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS		±2	±10	uA	VGS= ±20V VDS= 0V
2	IDSS			100	nA	VDS= 100V
3	BVDSS	105			V	ID= 10uA
4	Vth	1.5	2	2.5	V	ID= 250uA
5	RDS(on) 1		0.15	0.3	Ω	ID= 2.0A VGS= 10V
6	RDS(on) 2		0.16	0.35	Ω	ID= 1.0A VGS= 4.5V
7	VSD	0.5	0.75	1.1	V	IS= 1A VGS= 0V
8	Yfs	500			mS	VDS= 10V ID= 200mA

※ Built-in ZD between Gate and Source



NOTE: